

Radar Pulsed Power Transistor 5W, 3.1-3.5 GHz, 2µs Pulse, 10% Duty

M/A-COM Products Released, 10 Aug 07

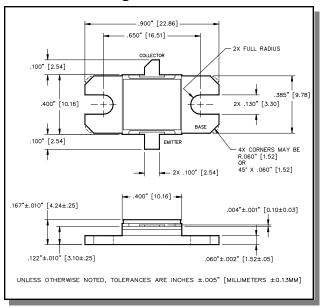
Features

- NPN silicon microwave power transistors
- · Common base configuration
- Broadband Class C operation
- High efficiency inter-digitized geometry
- · Diffused emitter ballasting resistors
- · Gold metallization system
- · Internal input and output impedance matching
- Hermetic metal/ceramic package
- RoHS compliant

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V_{CES}	60	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current (Peak)	Ic	0.75	Α
Power Dissipation @ +25°C	P _{TOT}	60	W
Storage Temperature	T _{STG}	-65 to +200	°C
Junction Temperature	T_J	200	°C

Outline Drawing



Electrical Specifications: T_C = 25 ± 5°C (Room Ambient)

Parameter	Test Conditions	Frequency	Symbol	Min	Max	Units
Collector-Emitter Breakdown Voltage	I _C = 10mA		BV _{CES}	60	-	V
Collector-Emitter Leakage Current	V _{CE} = 40V		I _{CES}	-	1.0	mA
Thermal Resistance	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	R _{TH(JC)}	1	3.5	°C/W
Output Power	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	P _{OUT}	5.0	-	W
Power Gain	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	G _P	8.5	=	dB
Collector Efficiency	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	ης	30	-	%
Input Return Loss	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	RL	-	-6	dB
Load Mismatch Tolerance	Vcc = 33V, Pin = 0.7W	F = 3.1, 3.3, 3.5 GHz	VSWR-T	-	2:1	-

PRELIMINARY: Data Sheets contain information regarding a product M/A-COM Technology Solutions has under development. Performance is based on engineering tests. Specifications are typical. Mechanical outline has been fixed. Engineering samples and/or test data may be available.

Commitment to produce in volume is not guaranteed.

North America Tel: 800.366.2266 / Fax: 978.366.2266

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Asia/Pacific Tel: 81.44.844.8296 / Fax: 81.44.844.8298
 Visit www.macomtech.com for additional data sheets and product information.

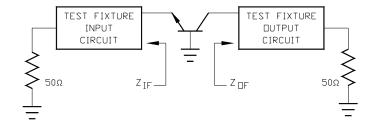


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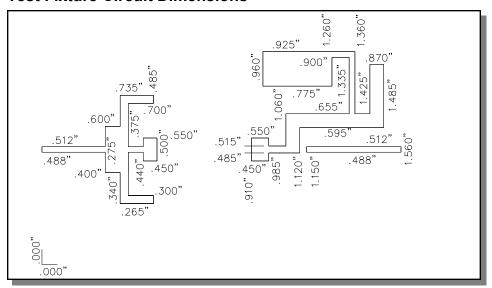
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RF Test Fixture Impedance

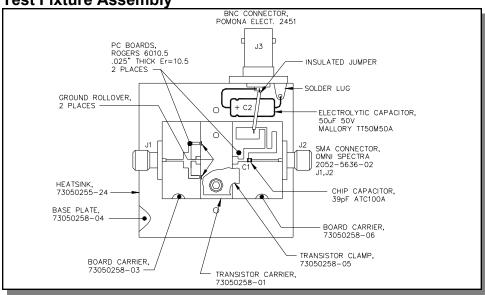
F (GHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
3.1	24 - j4.4	24 - j20
3.3	20 - j0.7	18 - j11
3.5	17 + j3.9	15 - j3.0



Test Fixture Circuit Dimensions



Test Fixture Assembly



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